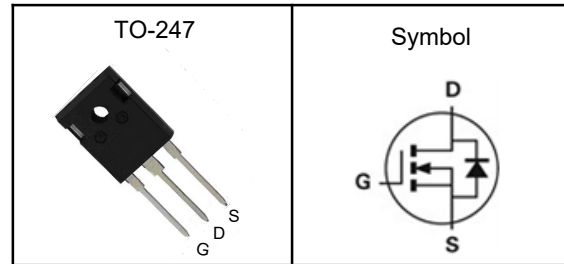


650V Super Junction Power MOSFET
Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.15\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.5$ to $3.5V$
- 100% avalanche tested
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- TV power & LED Lighting Power
- AC to DC Converters
- Telecom

Pin Description


V_{DSS}	650	V
$R_{DS(ON)-Typ}$	150	m Ω
I_D	21	A

Absolute Maximum Ratings ($T_J=25^\circ C$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit	
V_{DSS}	Drain-Source Voltage	650	V	
V_{GSS}	Gate-Source Voltage	± 30	V	
T_J	Maximum Junction Temperature	-55 to 150	$^\circ C$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$	
E_{AS}	Single Pulse Avalanche Energy ³	500	mJ	
$I_{DM}^{①}$	300 μs Pulse Drain Current Tested	52	A	
I_D	Continuous Drain Current	$T_C=25^\circ C$	21	A
P_D	Maximum Power Dissipation	$T_C=25^\circ C$	150	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (Max)	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	0.83	$^\circ C/W$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^\circ C$.

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.



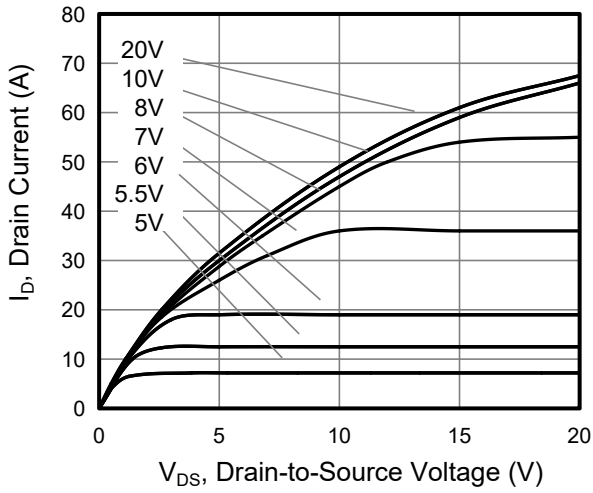
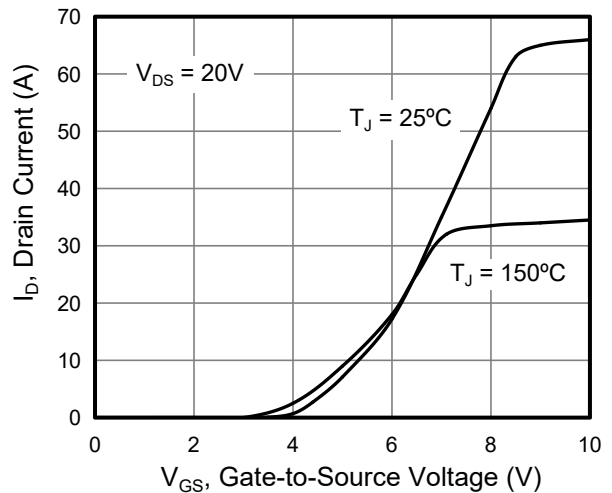
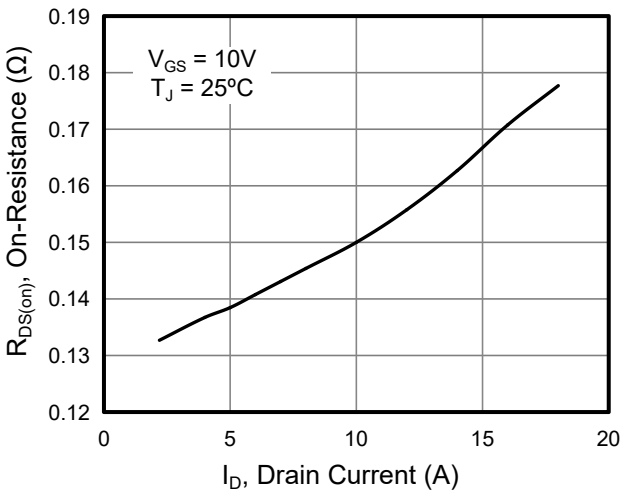
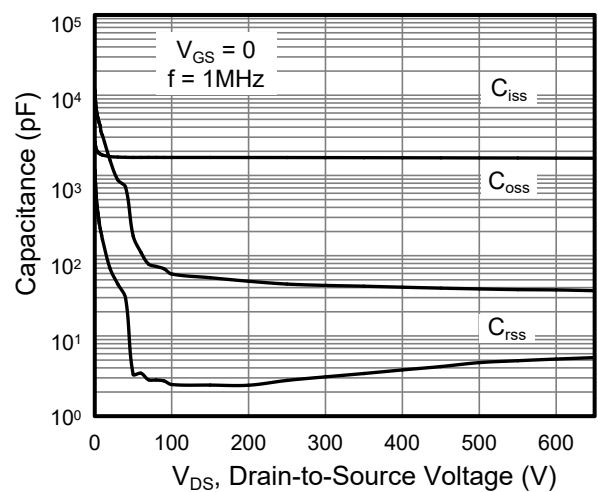
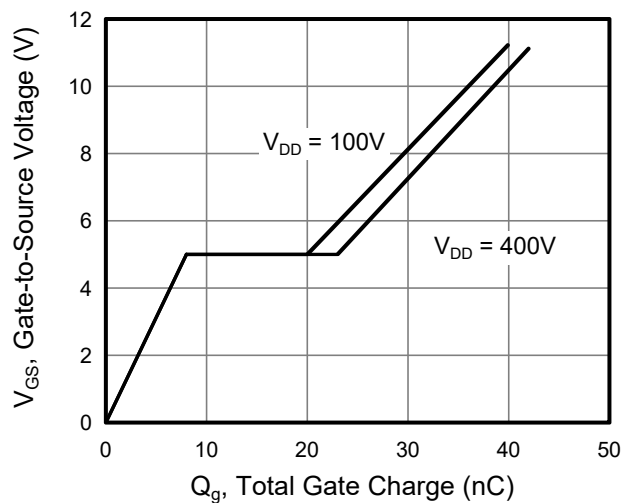
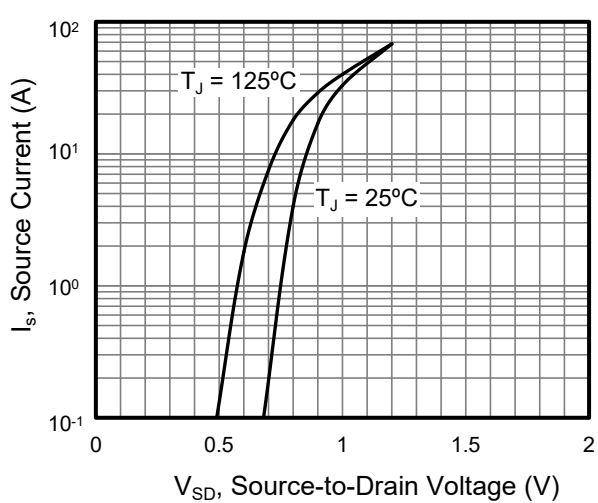
650V Super Junction Power MOSFET

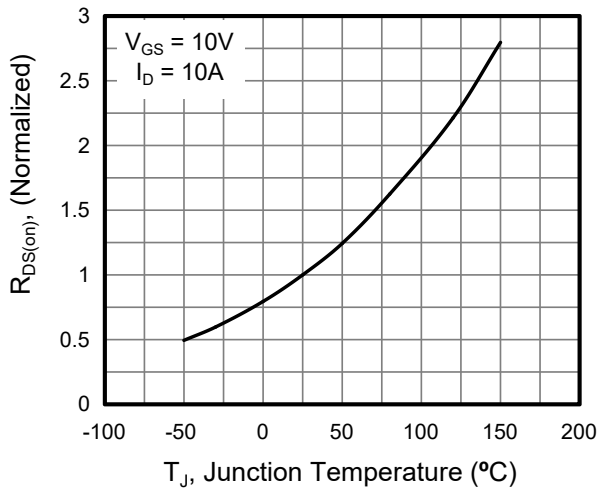
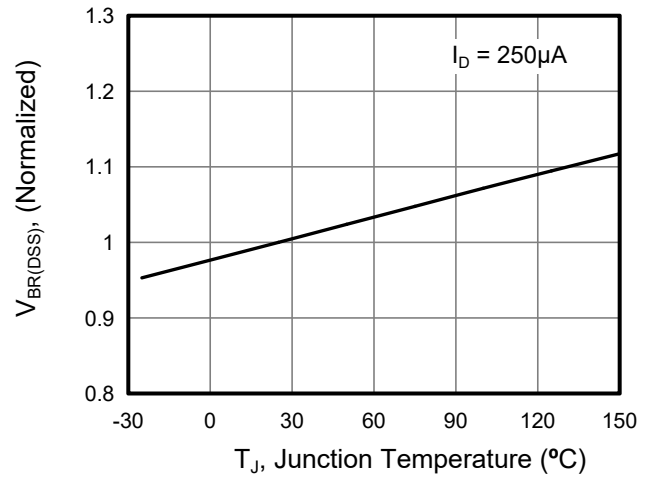
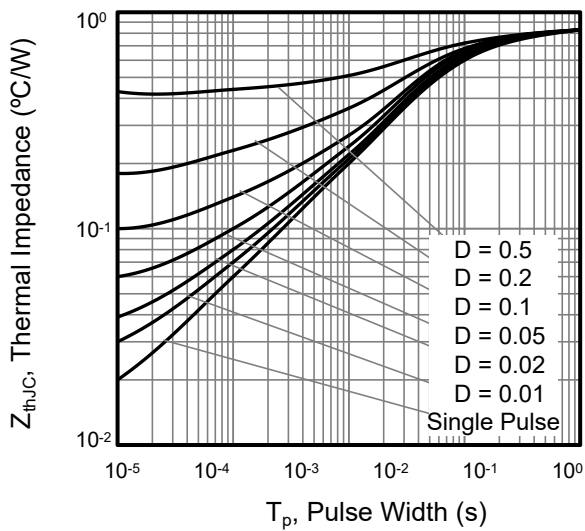
Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

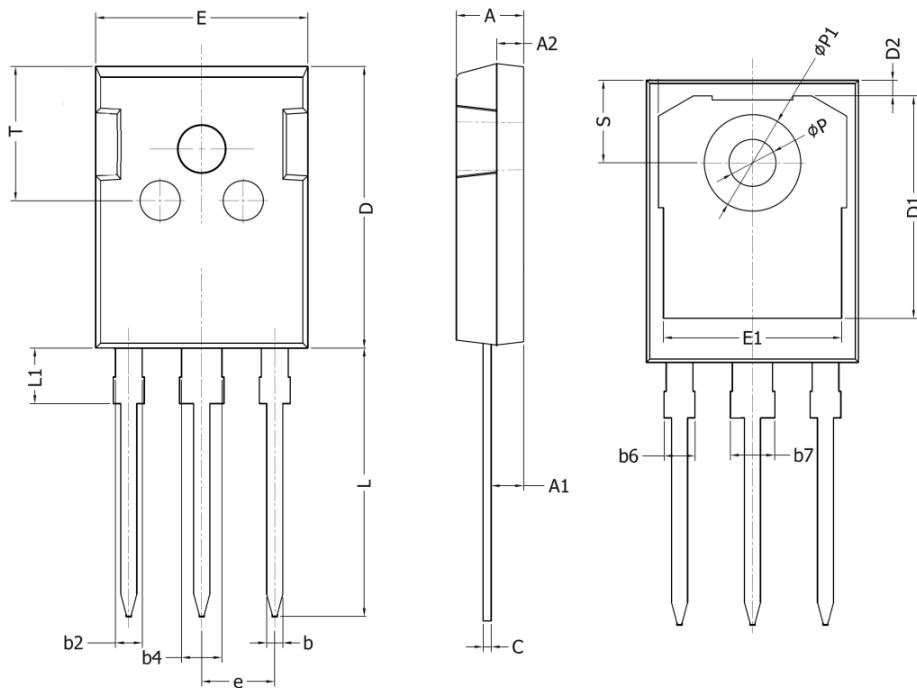
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250mA$	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	---	4.0	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=10A$	---	150	190	$m\Omega$
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=100V,$ $Freq.=1MHz$	---	1524	---	pF
C_{oss}	Output Capacitance		---	65	---	
C_{riss}	Reverse Transfer Capacitance		---	8	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=400V,$ $V_{GS}=10V, R_G=25\Omega,$ $I_D=20A$	---	25	---	nS
T_r	Turn-on Rise Time		---	59	---	
$T_{d(off)}$	Turn-off Delay Time		---	121	---	
T_f	Turn-off Fall Time		---	44	---	
Q_g	Total Gate Charge	$V_{DS}=400V,$ $V_{GS}=10V, I_D=20A$	---	40.5	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	15	---	
Source-Drain Characteristics ($T_J=25^{\circ}\text{C}$)						
V_{SD} ^④	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	---	0.9	1.2	V
t_{rr}	Reverse Recovery Time	$V_R=400V, I_F=20A,$ $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	453	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.1	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

650V Super Junction Power MOSFET
Typical Characteristics

Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance vs. Drain Current

Figure 4. Capacitance

Figure 5. Gate Charge

Figure 6. Body Diode Forward Voltage

650V Super Junction Power MOSFET

Figure 7. On-Resistance vs. Junction Temperature

Figure 8. Breakdown voltage vs. Junction Temperature

Figure 9. Transient Thermal Impedance

650V Super Junction Power MOSFET
TO-247 Package Outline Dimensions


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.90	5.20
A1	2.31	2.51
A2	1.9	2.1
b	1.16	1.26
b2	1.96	2.06
b4	2.96	3.06
b6	-	2.25
b7	-	3.25
C	0.59	0.66
D	20.90	21.20
D1	16.25	16.85
D2	1.05	1.35
E	15.75	16.10
E1	13.00	13.60
e	5.436 BSC	
L	19.80	20.20
L1	-	4.30
P	3.40	3.60
P1	7.00	7.40
S	6.05	6.25
T	9.80	10.20